

LL054BT23P6

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4-Channel Ultra Low Capacitance ESD Protection Diodes Array- 5.0V

Features

- Protects four I/O lines and one Vcc line
- Low capacitance
- Working voltages : 5V
- Low leakage current
- Low capacitance for high-speed interfaces
- No insertion loss to 2.0GHz
- Response time is <1ns
- Solid-state silicon avalanche technology
- RoHS compliant
- Provide transient protection:
IEC 61000-4-2 (ESD) meets level 4, 15kV(Air), 8kV(Contact)
IEC 61000-4-5 (Surge) 5A (8/20us)
- Suffix "-H" indicates Halogen-free parts, ex. LL054BT23P6-H

Mechanical data

- Epoxy : UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-23-6
- Terminals : Matte tin plated
- Mounting Position : Any
- Weight : Approximated 0.013 gram

Applications

- Digital visual interface (DVI)
- USB 1.1/2.0/OTG
- IEEE 1394 firewire ports
- Notebooks & handhelds
- Projection TV & monitors
- Set-top box
- Flat panel displays
- PCI express

Maximum ratings (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

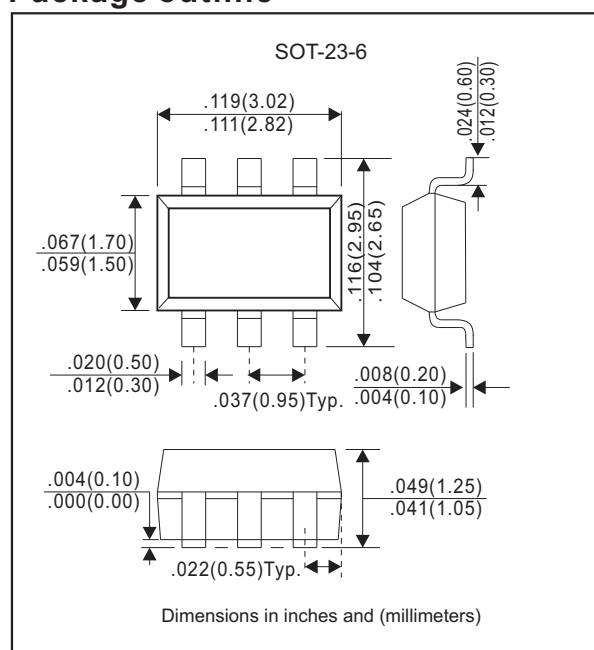
Parameter	Symbol	Value	Unit
Peak pulse power(8/20 μ s)	PPP	150	W
Peak pulse current (IEC 61000-4-5)	I _{PP}	5	A
ESD per IEC 61000-4-2(Air) ESD per IEC 61000-4-2(Contact)	V _{ESD}	± 15 ± 8	kV
Operating junction temperature range	T _J	-55 to +150	$^{\circ}\text{C}$
Storage temperature range	T _{STG}	-55 to +150	$^{\circ}\text{C}$

Electrical characteristics (at $T_A=25^{\circ}\text{C}$ unless otherwise noted)

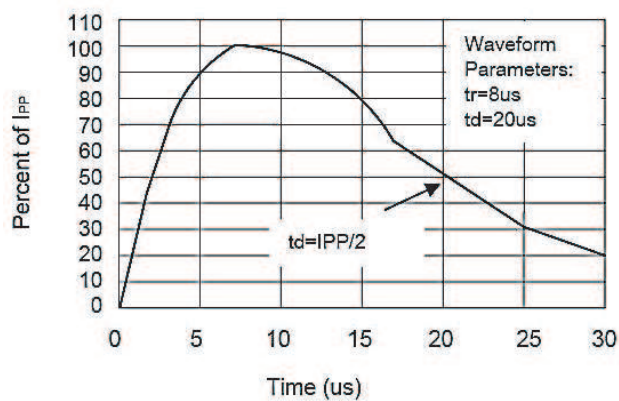
Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Reverse working voltage	any I/O pin to GND	V _{RWM}			5.0	V
Reverse breakdown voltage	I _T = 1mA, any I/O pin to GND	V _{BR}	6.0			V
Reverse leakage current	V _{RWM} = 5V, any I/O pin to GND	I _R			1.0	μA
Diode forward voltage	I _F = 15mA	V _F			1.2	V
Clamping voltage	I _{PP} = 1A, t _p = 8/20 μ s any I/O pin to GND	V _{C1}			15	V
Clamping voltage	I _{PP} = 5A, t _p = 8/20 μ s any I/O pin to GND	V _{C2}			28	V
Junction capacitance	V _R = 0V, f = 1MHz, between I/O pins	C _{J1}			0.40	pF
Junction capacitance	V _R = 0V, f = 1MHz, any I/O pin to GND	C _{J2}			0.80	pF

Note: I/O pins are pin 1,3,4,6.

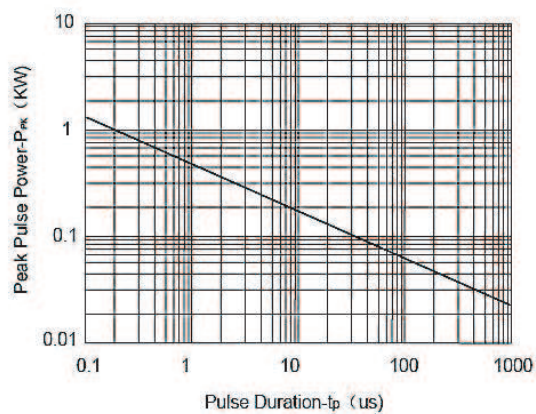
Package outline



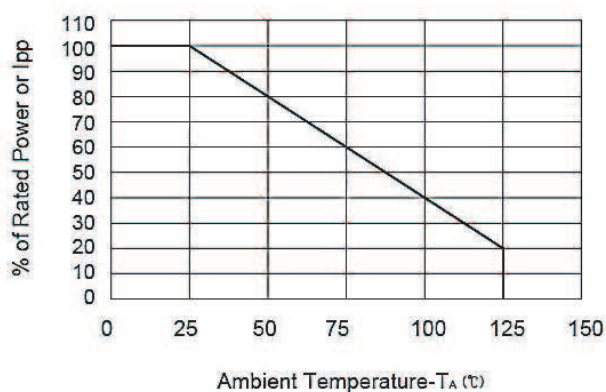
Rating and characteristic curves (LL054BT23P6)



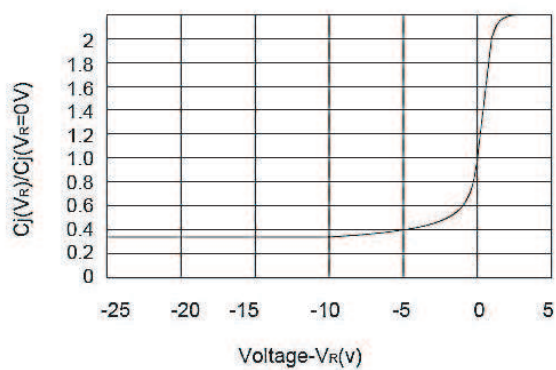
Pulse Waveform



Non-Repetitive Peak Pulse Power vs. Pulse Time



Power Derating Curve



Junction Capacitance vs. Reverse Voltage

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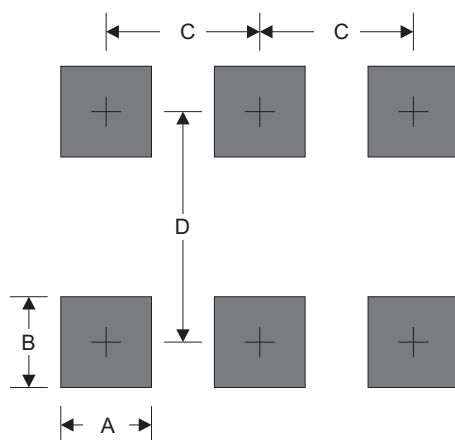
Pinning information

Pin Configuration	Simplified outline	Circuit Diagram

Marking

Type number	Marking code
LL054BT23P6	V05,V5L

Suggested solder pad layout

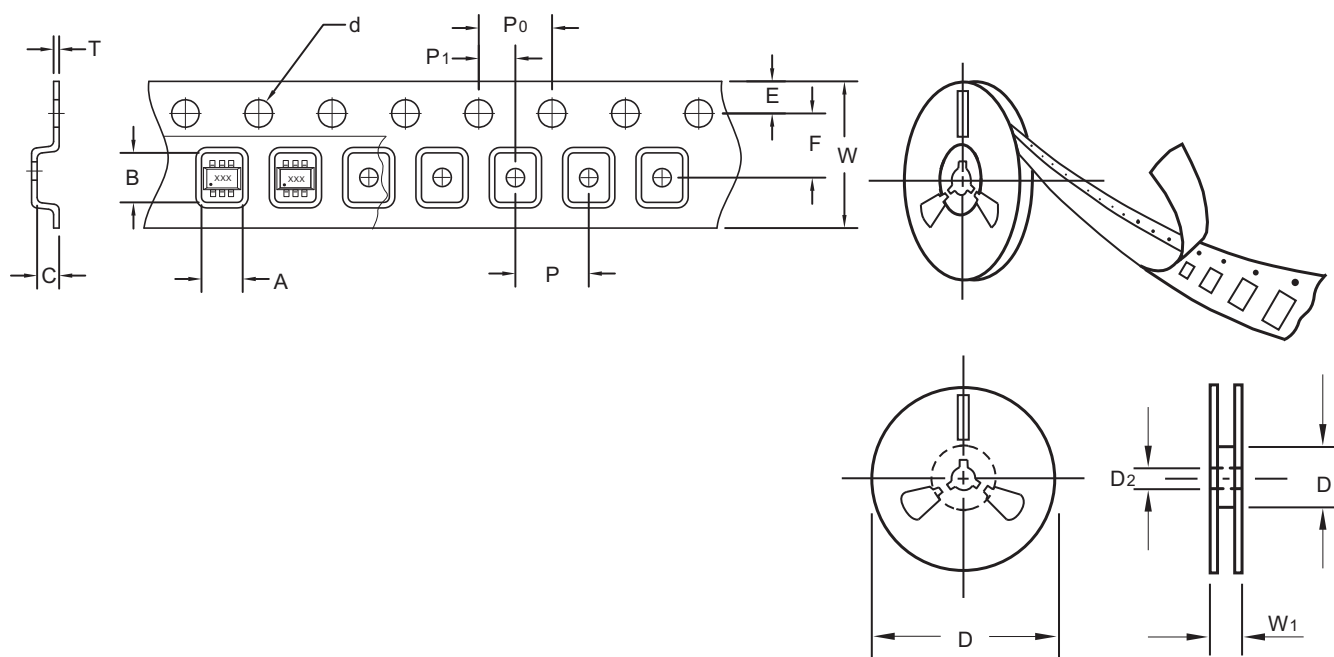


Dimensions in inches and (millimeters)

PACKAGE	A	B	C	D
SOT-23-6	0.028 (0.70)	0.039 (1.00)	0.037(0.95)	0.094(2.40)

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Packing information



unit:mm

Item	Symbol	Tolerance	SOT-23-6
Carrier width	A	0.1	3.25
Carrier length	B	0.1	3.20
Carrier depth	C	0.1	1.40
Sprocket hole	d	0.1	1.55
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	54.40
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.05	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.05	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	max	12.30

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

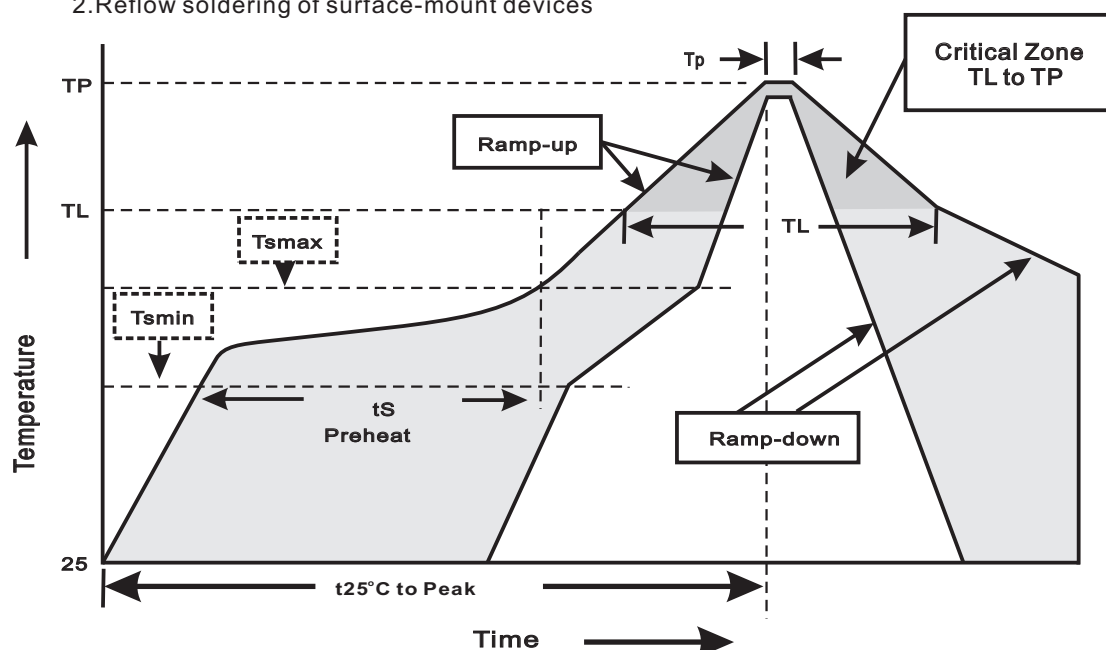
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)
SOT-23-6	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T_L to T_P)	$<3^{\circ}\text{C}/\text{sec}$
Preheat -Temperature Min(T_{min}) -Temperature Max(T_{max}) -Time(min to max)(t_s)	150°C 200°C 60~120sec
T_{max} to T_L -Ramp-upRate	$<3^{\circ}\text{C}/\text{sec}$
Time maintained above: -Temperature(T_L) -Time(t_L)	217°C 60~260sec
Peak Temperature(T_P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t_P)	10~30sec
Ramp-down Rate	$<6^{\circ}\text{C}/\text{sec}$
Time 25°C to Peak Temperature	$<6\text{minutes}$

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High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at 260±5°C for 10±2sec.	MIL-STD-750D METHOD-2031
2. Solderability	at 245±5°C for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_{BR} = V_{BR} \text{ Min} * 80\%$ at $T_J = 150^\circ\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Pressure Cooker	15P _{SIG} at $T_A = 121^\circ\text{C}$ for 4 hrs.	JESD22-A102
5. Temperature Cycling	-55°C to +125°C dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
6. Humidity	at $T_A = 85^\circ\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
7. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031